## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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In Re:		Wittich Kaule et al.	Confirmation No:	2401
Serial N	lo:	10/599,659	Group:	Not Yet Assigned
Filed:		October 4, 2006	Examiner:	Not Yet Assigned
For:		Device and method for producing resist profiled elements		
Custom	er No.:	29127		
Attorney No.	y Docket	0055.0013US1 (P-00060-WO/US)		
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Alexar	ndria, VA	22313-1450		
Sir:				
		sclosure Statement is submitted:		
[ ]		FR 1.129(a), or submission after Final Rejection)		
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[X]	(Within any o	FR 1.97(b), or ne of the following time periods: three months of filing nat attional stage in an international application; or before the m onal application, including a CPA, or a Request for Continu	ailing date of a first office action	
[]	under 37 C	FR 1.97(c) together with either:		
	[ ] a	Statement under 37 CFR 1.97(e), as checked be	low, or	
		\$180.00 fee under 37 CFR 1.17(p), or CFR 1.97(b) time period, but before final action or notice o	f allowance, whichever occurs	first)
[]	under 37 C	FR 1.97(d) together with:		
	[ ] a	Statement under 37 CFR 1.97(e), as checked be	low, and	
		\$180.00 fee under 37 CFR 1.17(p), or nal action or notice of allowance, whichever occurs first, bu	t on or before payment of the is	esue fee)
[ ]	Applicant	FR 1.97(i): requests that the IDS and cited reference(s) be properties that the IDS and cited reference (s) be properties the IDS and cited reference (s) be pr	placed in the application	filewrapper.

Statement Under 37 CFR 1.97(e)

Attorney Docket No: 0055.0013US1 (P-00060-WO/US)

[ ]	commu	em of information contained in this Information Disclosure Statement was first cited in any nication from a foreign patent office in a counterpart foreign application not more than onths prior to the filing of this Information Disclosure Statement; or						
[ ]	knowled in the in	No item of information contained in this Information Disclosure Statement was cited in a communication from a foreign patent office in a counterpart foreign application, and, to the knowledge of the undersigned, after making reasonable inquiry, no item of information contained in the information disclosure statement was known to any individual designated in 37 CFR 1.56(c) more than three months prior to the filing of this Information Disclosure Statement.						
Stateme	nt Under	37 CFR			other than design) filed on or			
[ ]	was not	nication fi received	rom a foreign patent of					
[X]	Enclose	d herewit	h is form PTO-1449:					
	[X]	Copies	of the cited references a	re enclosed except US paten	t references.			
	[]	References cited were entered in prior application, U.S. Application No. , to which priority under 35 U.S.C. 120 is claimed. [The earlier application contains copies of the cited references.]						
	[]	The listed references were cited in the enclosed International Search Report in a counterpart foreign application.						
	[X]		ncise explanation" requ CFR 1.98(a)(3) is satis	irement (non-English referen sfied by:	nces) for reference(s) [			
		[]	the explanation provid	led on the attached sheet.				
		[X]	the explanation provid	ed in the Specification.				
		[X]	submission of the encl	osed International Search Re	eport.			
		[]	submission of the encl and/or foreign Office		on of a foreign Search Report			
		[X]	the enclosed English la	anguage abstract.				
		[X]	the enclosed English la	anguage counterpart.				
[ ] Examiner's Initials	Applica	nt reques	s that the following no	n-published pending applica	tions be considered:			
		U.S. Pat	ent Application No. [	], by [inventor(s)], filed [	], Docket No.: [ ]			
		U.S. Pat	ent Application No. [	], by [inventor(s)], filed [	], Docket No.: [ ]			

		U.S. Patent Application No. [	], by [inventor(s)], filed [	], Docket No.: [ ]
		Examiner	Date	
	[ ]	A copy of each above-cited app	olication, including the curre	ent claims, is enclosed.
	[ ]	A copy of each above-cited app those entered in prior application 35 U.S.C. 120 is claimed.		ent claims, is enclosed, except ], to which priority under
		requested to return a copy of the considered with the next office c		cations indicating which
It is req	uested th	at the information disclosed here	in be made of record in this	application.
Method	of paym	ent:		
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			Respectfully s	ubmitted,
			Houston Elise	eva LLP
			By Maria Elisee Registration	ys Elseus Eva No. 43,328
Dated:	October	5, 2006		

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Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number. Complete if Known Substitute for form 1449/PTO Application Number 10/599.659 Filing Date October 4, 2006 INFORMATION DISCLOSURE First Named Inventor Wittich Kaule et al. STATEMENT BY APPLICANT Art Unit Not Yet Assigned (Use as many sheets as necessary) Examiner Name Not Yet Assigned

0055.0013US1 (P-00060) Sheet 1 Attorney Docket Number of 2 U. S. PATENT DOCUMENTS Pages, Columns, Lines, Where Relevant Passages or Relevant Cite No.1 Document Number Publication Date Name of Patentee or MM-DD-YYYY Initials\* Applicant of Cited Document Figures Appear Number-Kind Code<sup>2</sup> (# known) US- 5.566,023 10/15/1996 Ernst-Bernhard Klev HS-HS. US-US-US-US-US-US US-US-US-US-US-119. US-US-110

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No.	Foreign Patent Document	Publication Date	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages	l .
		Country Code <sup>3 "</sup> Number <sup>4</sup> "Kind Code <sup>3</sup> (if known)	MM-DD-YYYY		Or Relevant Figures Appear	T <sup>6</sup>
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		EP0648343	04/19/1995	Ernst-Bernhard Kley		
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This collection of information is required by 37 CFR 1.97 and 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete, including gathering, prepering, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, P.O. Box 1450, Alexandria, Va 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, Va 22313-1450.

PTO/SB/08B (07-06)

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Substitute for form 1449/PTO				Complete if Known		
Supplie	ite for form 1448# 10			Application Number	10/599,659	
INF	ORMATION	I DIS	SCLOSURE	Filing Date	October 4, 2006	
STATEMENT BY APPLICANT			PPLICANT	First Named Inventor	Wittich Kaule et al.	-
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(Use as many sheets as necessary)			necessary)	Examiner Name	Not Yet Assigned	
Sheet	2	of	2	Attorney Docket Number	0055.0013US1 (P-00060)	

	NON PATENT LITERATURE DOCUMENTS	
Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T²
	KLEY, E. et al. E-Beam lithography: a suitable technology for fabrication of high-accuracy Proceedings of the SPIE, 10/23/1995, p.71-80, v.2640, SPIE, Bellingham, VA, US.	
	SCHNABEL, B. et al. Fabrication and application of subwavelength gratings. Proceedings of the SPIE, 2/10/1997, p.233-41, v.3008, SPIE, Bellingham, VA, US.	
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	JAGDHOLD, U. et al. 60nm copper lines produced by a lift-off technique with 5keV electrons Proceedings of the SPIE, 1997, p.757-64, v.3049, SPIE, Bellingham, VA, US.	
	HAM, Y. et al. Application of a new empirical model to the electron beam lithography Japanese Journal of Applied Physics, 12/1998, p.6761-66, v.37, n.12B, JSAP, Tokyo, JP.	
	WITTIG, L. et al. Intermittence effect in electron beam writing. Microelectronic Engineering, 9/2001, p.321-6, v.57-58, Elsevier Publishers, Amsterdam, NL.	
	Cite No.1	No.1 the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.  KLEY, E. et al. E-Beam lithography: a suitable technology for fabrication of high-accuracy Proceedings of the SPIE, 10/23/1995, p.71-80, v.2640, SPIE, Bellingham, VA, US.  SCHNABEL, B. et al. Fabrication and application of subwavelength gratings. Proceedings of the SPIE, 2/10/1997, p.233-41, v.3008, SPIE, Bellingham, VA, US.  HEIDENRICH, R. et al. Electron scattering and line profiles in negative electron resists. Journal of Vacuum Science and Technology, 11/1976, p.1284-88, v.12, n.6, AVS, NY, US.  LIN, L. Cross-section profiles of single-scan negative electron-resist lines. Journal of Vacuum Science and Technology, 11/1976, p.1289-93, v.12, n.6, AVS, NY, US.  JAGDHOLD, U. et al. 60nm copper lines produced by a lift-off technique with 5keV electrons Proceedings of the SPIE, 1997, p.757-64, v.3049, SPIE, Bellingham, VA, US.  HAM, Y. et al. Application of a new empirical model to the electron beam lithography Japanese Journal of Applied Physics, 12/1998, p.6761-66, v.37, n.12B, JSAP, Tokyo, JP.  WITTIG, L. et al. Intermittence effect in electron beam writing. Microelectronic

Examiner	Date	
Signature	Considered	

<sup>\*</sup>EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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1 Applicant's unique distation designation number (optional). 2 Applicant is to place a check mark here If English language Translation is attached. This collection of information is required by 37 CFR 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, shotle be sent to the Christ Information Officer, U.S. Patent and Trademark Office, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

## INTERNATIONAL SEARCH REPORT

PCT/FP2005/051451

			1, 2, 2000, 001.22			
A. CLASSIFICATION OF SUBJECT MATTER G03F7/20 H01J37/317 G11B11/00						
According to	According to International Patent Classification (IPC) or to both national classification and IPC					
B. FIELDS	SEARCHED					
Minimum do	cumentation searched (classification system followed by classification \$11B H01J 603F	n symbols)				
	Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched					
	ata base consulted during the international search (name of data bas ternal, INSPEC, IBM—TDB, WPI Data, P		h terms used)			
C. DOCUME	ENTS CONSIDERED TO BE RELEVANT					
Category °	Citation of document, with indicalion, where appropriate, of the rele	vant passages	Relevant to claim No.			
A	KLEY E-B ET AL: "E-BEAM LITHOGRAPHY: A SUITABLE TECHNOLOGY FOR FABRICATION OF HIGH-ACCURACY 2D AND 3D SURFACE PROFILES" PROCEEDINGS OF THE SPIE, SPIE, BELLINGHAM, VA, US, vol. 2640, 23 October 1995 (1995-10-23), pages 71-80, XP009031977 ISSN: 0277-786X the whole document  SCHNABEL B ET AL: "FABRICATION AND APPLICATION OF SUBWAVELENGTH GRATINGS" PROCEEDINGS OF THE SPIE, SPIE, BELLINGHAM, VA, US, vol. 3008, 10 February 1997 (1997-02-10),		1-30			
	pages 233-241, XP009031976 ISSN: 0277-786X 	/				
χ Furti	her documents are listed in the $$ continuation of box $$ C.	Patent family member	ers are listed in annex.			
*Special categories of cited documents:  *A* document defining the general state of the art which is not considered to be of particular relevance to set of particular relevance; the claimed invention which is cet do o eablish the publication date of another clatton or other special reason (as specified)  **O' document referring to an oral disclosure, use, exhibition or o'ther means  **Pa' document published after the international filing date but lister than the priority date claimed filing date but  **Take the document published after the international filing date or priority date claimed invention of the same patent family  **Take the document published after the international filing date or priority date and not in continct with the application but in consistence to set of understance to the countent of particular relevance; the claimed invention own to exhibit the priority of comment relevance; the claimed invention or o'ther means.  **Take the occument of particular relevance; the claimed invention own to be considered to common to store a particular relevance; the claimed invention own to be considered to the priority of comment relevance; the claimed invention own to be considered to the priority of comment relevance; the claimed invention own to be considered to the priority of comment relevance; the claimed invention own to be considered to the priority of comment relevance; the claimed invention own to be considered to the priority of comment relevance; the claimed invention own to be considered to the priority of comment relevance; the claimed invention own to be considered to the priority of comment relevance; the claimed invention own to be comment of particular relevance; the claimed invention own to be comment of particular relevance; the claimed invention own to be considered to the						
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## INTERNATIONAL SEARCH REPORT

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	ation) DOCUMENTS CONSIDERED TO BE RELEVANT	
Category °	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
А	HEIDENREICH R D ET AL: "Electron scattering and line profiles in negative electron resists" JOURNAL OF VACUUM SCIENCE AND TECHNOLOGY USA, vol. 12, no. 6, November 1976 (1976-11), pages 1284-1288, XP002375481 ISSN: 0022-5355	
A	LIN L H: "Cross-section profiles of single-scan negative electron-resist lines"  JOURNAL OF VACUUM SCIENCE AND TECHNOLOGY USA,  vol. 12, no. 6, November 1976 (1976-11), pages 1289-1293, XP002375482 ISSN: 0022-5355	
x	JAGDHOLD U ET AL: "60 nm copper lines produced by a lift-off technique with 5 keV electrons: experiment and simulation" PROCEEDINGS OF THE SPIE - THE INTERNATIONAL SOCIETY FOR OPTICAL ENGINEERING SPIE-INT. SOC. OPT. ENG USA, vol. 3049, 1997, pages 757-764, XP002375483 ISSN: 0277-786X the whole document	1,2,5-8, 12-14, 21,24
A	HAM Y-M ET AL: "APPLICATION OF A NEW EMPIRICAL MODEL TO THE ELECTRON BEAM LITHOGRAPHY PROCESS WITH CHEMICALLY AMPLIFIED RESIST"  JAPANESE JOURNAL OF APPLIED PHYSICS, JAPAN SOCIETY OF APPLIED PHYSICS, TOKYO, JP, vol. 37, no. 12B, December 1998 (1998-12), pages 6761-6766, XP000880252  ISSN: 0021-4922	
Α	WITTIG L-CHR ET AL: "Intermittence effect in electron beam writing" MICROELECTRONIC ENGINEERING, ELSEVIER PUBLISHERS BY., AMSTERDAM, NL, vol. 57-58, September 2001 (2001-09), pages 321-326, XP004302280 ISSN: 0167-9317	